

B1  
a low reflection film coated on a second end of the multi-layer film opposite to the first end and comprising essentially  $\text{Al}_2\text{O}_3$  having a resistivity of  $1 \times 10^{12} \Omega \cdot \text{m}$  or more.

---

8. (Amended) A semiconductor laser device comprising:  
a semiconductor multi-layer film formed by laminating optical confinement layers and active layers so as to dispose each of said active layers between said optical confinement layers;

B2  
a high reflection film coated on a first end of the multi-layer film perpendicular to junction planes of the individual layers in said semiconductor multi-layer film; and

a low reflection film coated on a second end of the multilayer film opposite to the first end and comprising essentially  $\text{Al}_2\text{O}_3$  having a stoichiometric ratio composition.

---

18. (Amended) A semiconductor laser device comprising:  
a semiconductor multi-layer film comprising at least one confinement layer and at least one active layer;

B3  
a high reflection film substantially perpendicular to the semiconductor multi-layer film; and

—  
a low reflection film substantially perpendicular to the semiconductor multi-layer film, wherein the low reflection film comprises essentially  $\text{Al}_2\text{O}_3$  having a stoichiometric ratio composition.

---

Please add Claim 20 as follows:

---

20. (New) A semiconductor laser device comprising: